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SiM3C1xx

High-Performance, Low-Power, 32-Bit Precision32™ MCU Family with up to 256 kB of Flash

32-bit ARM® Cortex™-M3 CPU

- 80 MHz maximum frequency
- Single-cycle multiplication, hardware division support
- Nested vectored interrupt control (NVIC) with 16 priority levels

Memory

- 32–256 kB Flash, in-system programmable
- 8–32 kB SRAM (including 4 kB retention SRAM)
- 16-channel DMA controller
- External bus interface supports up to 16 MB of external memory and a parallel LCD interface with QVGA resolution

Power Management

- Low drop-out (LDO) regulator
- Power-on reset circuit and brownout detectors
- 5-to-3.3 V 150 mA regulator supports up to 5 V input supply
- Adjustable external regulator supports up to 3.6 V, 1000 mA
- Multiple power modes supported for low power optimization

Low Power Features

- 85 nA current mode with voltage supply monitor enabled
- Low-current RTC: 350 nA internal LFO, 620 nA external crystal
- 12 µs wakeup (lowest power mode); 1.5 µs analog setting time
- 275 µA/MHz active current
- Clocks can be gated off from unused peripherals to save power
- Flexible clock divider: Reduce operational frequency up to 128x

Clock Sources

- Internal oscillator with PLL: 23–80 MHz, reduced EMI mode
- Low power internal oscillator: 20 MHz and 2.5 MHz modes
- Low frequency internal oscillator: 16.4 kHz
- External oscillators: Crystal, RC, C, CMOS and RTC Crystal

Temperature Range: –40 to +85 °C

Package Options

- QFN options: 40-pin (6 x 6 mm), 64-pin (9 x 9 mm)
- TQFP options: 64-pin (10 x 10 mm), 80-pin (12 x 12 mm)
- LGA option: 92-pin (7 x 7 mm)

Analog Peripherals

- 2 x 12-Bit Analog-to-Digital Converters: Up to 250 ksps 12-bit mode or 1 Msps 10-bit mode, internal or external reference
- 2 x 10-Bit Current-mode Digital-to-Analog Converters, four-word buffer enables 12-bit operation
- 2 x Low-current comparators
- 16-Channel Capacitance-to-Digital: Fast, <1 µA wake-on-touch
- 2 x Current-to-Voltage Converter, up to 6 mA input range

Digital and Communication Peripherals

- 2 x USARTs and 2 x UARTs with IrDA and ISO7816 SmartCard
- 3 x SPIs, 2 x I2C, I^2S (receive and transmit), 16/32-bit CRC
- 128/192/256-bit Hardware AES Encryption

Timers/Counters

- 2 x 32-bit or 4 x 16-bit timers with capture/compare
- 2 x 16-bit, 2-channel counters with capture/compare/PWM
- 16-bit, 6-channel counter with capture/compare/PWM and dead-time controller with differential outputs
- 16-bit low power timer/pulse counter operational in sleep
- 32-bit real time clock (RTC) with multiple alarms
- Watchdog timer

Up to 65 Flexible I/O

- Up to 59 contiguous GPIO with two priority crossbars providing flexibility in pin assignments; 12 x 5 V tolerant GPIO
- Up to 6 programmable high drive capable (5–300 mA, 1.8–6 V) I/O can drive LEDs, power MOSFETs, buzzers, etc.

On-Chip Debugging

- Serial wire debug (SWD) or JTAG (no boundary scan), serial wire viewer (SWV)
- Cortex-M3 embedded trace macrocell (ETM)

Supply Voltage

- 2.7 to 5.5 V (regulator enabled)
- 1.8 to 3.6 V (regulator disabled)

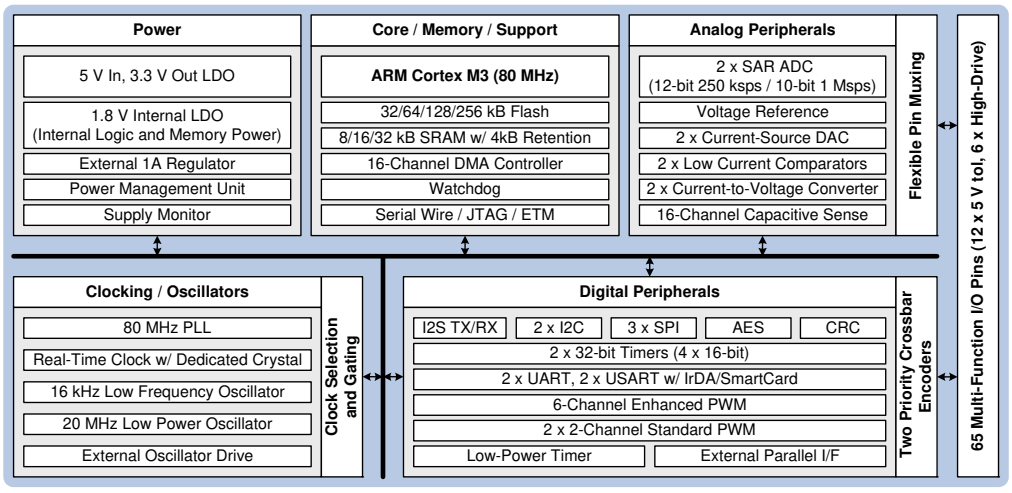

Table of Contents

1. Related Documents and Conventions

1.1. Related Documents

This data sheet accompanies several documents to provide the complete description of the SiM3C1xx device family.

1.1.1. SiM3U1xx/SiM3C1xx Reference Manual

The Silicon Laboratories SiM3U1xx/SiM3C1xx Reference Manual provides detailed functional descriptions for the SiM3C1xx devices.

1.1.2. Hardware Access Layer (HAL) API Description

The Silicon Laboratories Hardware Access Layer (HAL) API provides C-language functions to modify and read each bit in the SiM3C1xx devices. This description can be found in the SiM3xxxx HAL API Reference Manual.

1.1.3. ARM Cortex-M3 Reference Manual

The ARM-specific features like the Nested Vector Interrupt Controller are described in the ARM Cortex-M3 reference documentation. The online reference manual can be found here:
http://infocenter.arm.com/help/topic/com.arm.doc.subset.cortexm.m3/index.html#cortexm3.

1.2. Conventions

The block diagrams in this document use the following formatting conventions:

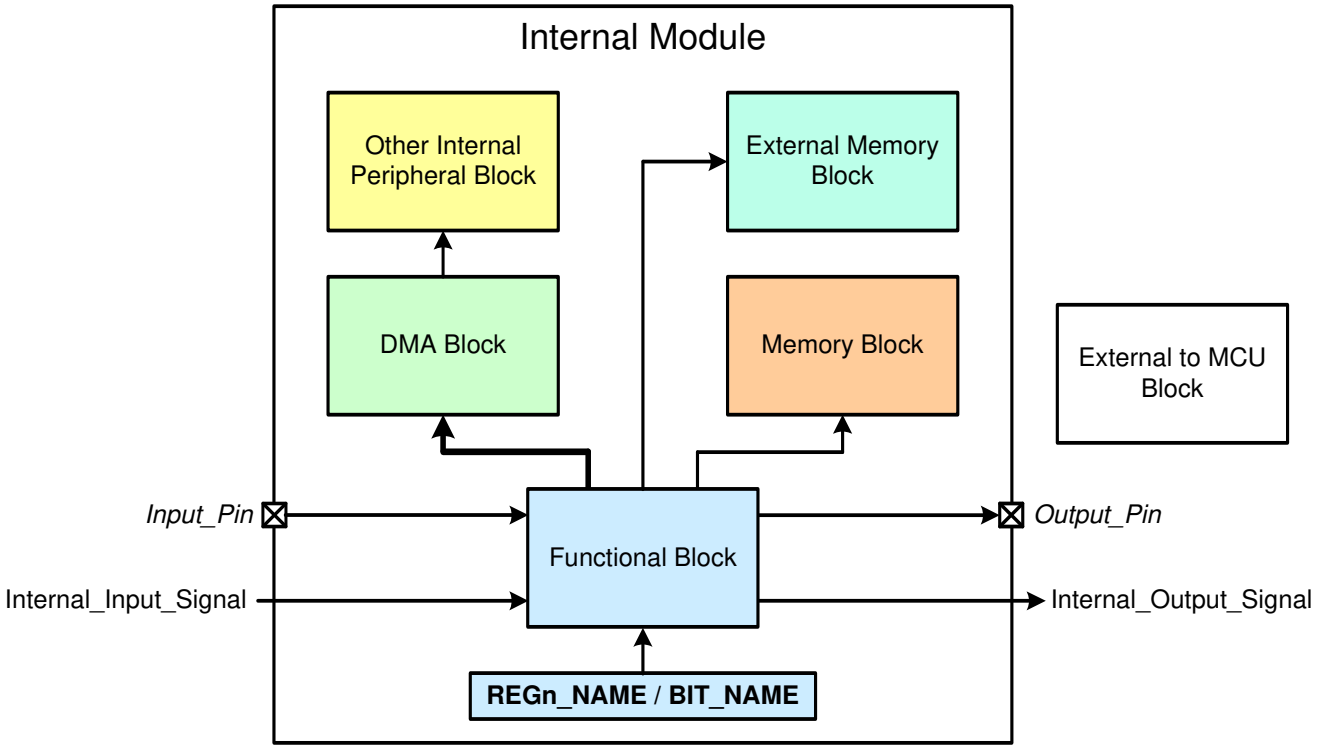

Figure 1.1. Block Diagram Conventions

2. Typical Connection Diagrams

This section provides typical connection diagrams for SiM3C1xx devices.

2.1. Power

Figure 2.1 shows a typical connection diagram for the power pins of the SiM3C1xx devices when the internal regulator is in use.

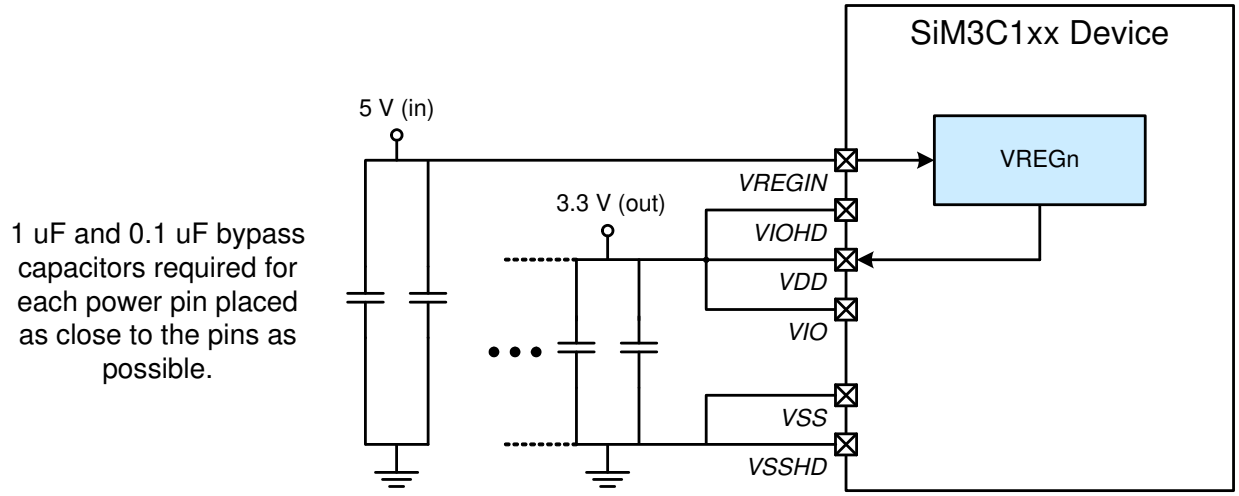

Figure 2.1. Connection Diagram with Voltage Regulator Used

Figure 2.2 shows a typical connection diagram for the power pins of the SiM3C1xx devices when the internal regulator is not used.

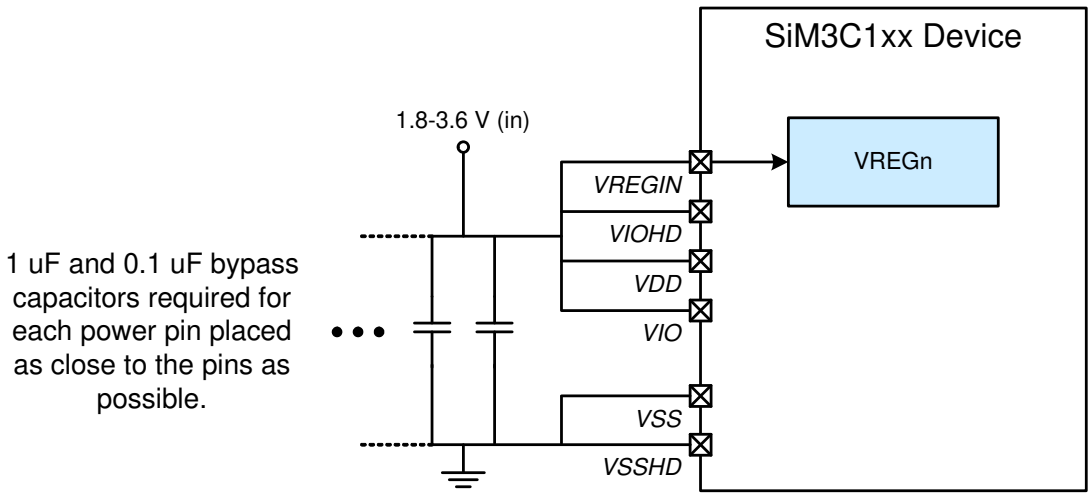

Figure 2.2. Connection Diagram with Voltage Regulator Not Used

3. Electrical Specifications

3.1. Electrical Characteristics

All electrical parameters in all tables are specified under the conditions listed in Table 3.1, unless stated otherwise.

Table 3.1. Recommended Operating Conditions

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Operating Supply Voltage on VDD	V_{DD}		1.8	—	3.6	V
Operating Supply Voltage on VREGIN	V_{REGIN}	EXTVREG0 Not Used	4	—	5.5	V
		EXTVREG0 Used	3.0	—	3.6	V
Operating Supply Voltage on VIO	V_{IO}		1.8	—	V_{DD}	V
Operating Supply Voltage on VIOHD	V_{IOHD}	HV Mode (default)	2.7	—	6.0	V
		LV Mode	1.8	—	3.6	V
Voltage on I/O pins, Port Bank 0, 1 and 2 I/O	V_{IN}		V_{SS}	—	V_{IO}	V
Voltage on I/O pins, Port Bank 3 I/O and $\overline{\text{RESET}}$	V_{IN}	SiM3C1x7 PB3.0–PB3.7 and $\overline{\text{RESET}}$	V_{SS}	—	V_{IO}+2.0	V
		SiM3C1x7 PB3.8 - PB3.11	V_{SS}	—	Lowest of V_{IO}+2.0 or V_{REGIN}	V
		SiM3C1x6 PB3.0–PB3.5 and $\overline{\text{RESET}}$	V_{SS}	—	V_{IO}+2.0	V
		SiM3C1x6 PB3.6–PB3.9	V_{SS}	—	Lowest of V_{IO}+2.0 or V_{REGIN}	V
		SiM3C1x4 $\overline{\text{RESET}}$	V_{SS}	—	V_{IO}+2.0	V
		SiM3C1x4 PB3.0–PB3.3	V_{SS}	—	Lowest of V_{IO}+2.0 or V_{REGIN}	V
Voltage on I/O pins, Port Bank 4 I/O	V_{IN}		V_{SSHD}	—	V_{IOHD}	V
System Clock Frequency (AHB)	f_{AHB}		0	—	80	MHz
Peripheral Clock Frequency (APB)	f_{APB}		0	—	50	MHz
Operating Ambient Temperature	T_A		–40	—	85	°C
Operating Junction Temperature	T_J		–40	—	105	°C

Note: All voltages with respect to V_{SS}.

Table 3.2. Power Consumption

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Digital Core Supply Current						
Normal Mode[2,3,4,5]—Full speed with code executing from Flash, peripheral clocks ON	I_{DD}	F_{AHB} = 80 MHz, F_{APB} = 40 MHz	—	33	36.5	mA
		$F_{AHB} = F_{APB}$ = 20 MHz	—	10.5	13.3	mA
		$F_{AHB} = F_{APB}$ = 2.5 MHz	—	2.0	3.8	mA
Normal Mode[2,3,4,5]—Full speed with code executing from Flash, peripheral clocks OFF	I_{DD}	F_{AHB} = 80 MHz, F_{APB} = 40 MHz	—	22	24.9	mA
		$F_{AHB} = F_{APB}$ = 20 MHz	—	7.8	10	mA
		$F_{AHB} = F_{APB}$ = 2.5 MHz	—	1.2	3	mA
Power Mode 1[2,3,4,6]—Full speed with code executing from RAM, peripheral clocks ON	I_{DD}	F_{AHB} = 80 MHz, F_{APB} = 40 MHz	—	30.5	35.5	mA
		$F_{AHB} = F_{APB}$ = 20 MHz	—	8.5	—	mA
		$F_{AHB} = F_{APB}$ = 2.5 MHz	—	1.7	—	mA
Power Mode 1[2,3,4,6]—Full speed with code executing from RAM, peripheral clocks OFF	I_{DD}	F_{AHB} = 80 MHz, F_{APB} = 40 MHz	—	20	23	mA
		$F_{AHB} = F_{APB}$ = 20 MHz	—	5.3	—	mA
		$F_{AHB} = F_{APB}$ = 2.5 MHz	—	1.0	—	mA
Power Mode 2[2,3,4]—Core halted with peripheral clocks ON	I_{DD}	F_{AHB} = 80 MHz, F_{APB} = 40 MHz	—	19	22	mA
		$F_{AHB} = F_{APB}$ = 20 MHz	—	7.8	—	mA
		$F_{AHB} = F_{APB}$ = 2.5 MHz	—	1.3	—	mA
Power Mode 3[2,3]	I_{DD}	V_{DD} = 1.8 V, T_A = 25 °C	—	175	—	µA
		V_{DD} = 3.0 V, T_A = 25 °C	—	250	—	µA

Notes:
1. Perhipheral currents drop to zero when peripheral clock and peripheral are disabled, unless otherwise noted.
2. Currents are additive. For example, where I_{DD} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
3. Includes all peripherals that cannot have clocks gated in the Clock Control module.
4. Includes supply current from internal regulator and PLL0OSC (>20 MHz) or LPOSC0 (<=20 MHz).
5. Flash execution numbers use 2 wait states for 80 MHz and 0 wait states at 20 MHz or less.
6. RAM execution numbers use 0 wait states for all frequencies.
7. IDAC output current and IVC input current not included.
8. Bias current only. Does not include dynamic current from oscillator running at speed.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 9[2,3]—Low Power Shutdown with VREG0 disabled, powered through VDD and VIO	I_{DD}	RTC Disabled, V_{DD} = 1.8 V, T_A = 25 °C	—	85	—	nA
		RTC w/ 16.4 kHz LFO, V_{DD} = 1.8 V, T_A = 25 °C	—	350	—	nA
		RTC w/ 32.768 kHz Crystal, V_{DD} = 1.8 V, T_A = 25 °C	—	620	—	nA
		RTC Disabled, V_{DD} = 3.0 V, T_A = 25 °C	—	145	—	nA
		RTC w/ 16.4 kHz LFO, V_{DD} = 3.0 V, T_A = 25 °C	—	500	—	nA
		RTC w/ 32.768 kHz Crystal, V_{DD} = 3.0 V, T_A = 25 °C	—	800	—	nA
Power Mode 9[2,3]—Low Power Shutdown with VREG0 in low-power mode, VDD and VIO powered through VREG0 (Includes VREG0 current)	I_{VREGIN}	RTC Disabled, VREGIN = 5 V, T_A = 25 °C	—	300	—	nA
		RTC w/ 16.4 kHz LFO, VREGIN = 5 V, T_A = 25 °C	—	650	—	nA
		RTC w/ 32.768 kHz Crystal, VREGIN = 5 V, T_A = 25 °C	—	950	—	nA
VIOHD Current (High-drive I/O disabled)	I_{VIOHD}	HV Mode (default)	—	2.5	5	µA
		LV Mode	—	2	—	nA

Notes:

1. Perhipheral currents drop to zero when peripheral clock and peripheral are disabled, unless otherwise noted.
2. Currents are additive. For example, where I_{DD} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
3. Includes all peripherals that cannot have clocks gated in the Clock Control module.
4. Includes supply current from internal regulator and PLL0OSC (>20 MHz) or LPOSC0 (<=20 MHz).
5. Flash execution numbers use 2 wait states for 80 MHz and 0 wait states at 20 MHz or less.
6. RAM execution numbers use 0 wait states for all frequencies.
7. IDAC output current and IVC input current not included.
8. Bias current only. Does not include dynamic current from oscillator running at speed.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Analog Peripheral Supply Currents						
Voltage Regulator (VREG0)	I_{VREGIN}	Normal Mode, T_A = 25 °C BGDIS = 0, SUSEN = 0	—	300	—	µA
		Normal Mode, T_A = 85 °C BGDIS = 0, SUSEN = 0	—	—	650	µA
		Suspend Mode, T_A = 25 °C BGDIS = 0, SUSEN = 1	—	75	—	µA
		Suspend Mode, T_A = 85 °C BGDIS = 0, SUSEN = 1	—	—	115	µA
		Sleep Mode, T_A = 25 °C BGDIS = 1, SUSEN = X	—	90	—	nA
		Sleep Mode, T_A = 85 °C BGDIS = 1, SUSEN = X	—	—	500	nA
Voltage Regulator (VREG0) Sense	$I_{VRSENSE}$	SENSEEN = 1	—	3	—	µA
External Regulator (EXTVREG0)	$I_{EXTVREG}$	Regulator	—	215	250	µA
		Current Sensor	—	7	—	µA
PLL0 Oscillator (PLL0OSC)	I_{PLLOSC}	Operating at 80 MHz	—	1.75	1.86	mA
Low-Power Oscillator (LPOSC0)	I_{LPOSC}	Operating at 20 MHz	—	190	—	µA
		Operating at 2.5 MHz	—	40	—	µA
Low-Frequency Oscillator (LFOSC0)	I_{LFOSC}	Operating at 16.4 kHz, T_A = 25 °C	—	215	—	nA
		Operating at 16.4 kHz, T_A = 85 °C	—	—	500	nA

Notes:

1. Perhipheral currents drop to zero when peripheral clock and peripheral are disabled, unless otherwise noted.
2. Currents are additive. For example, where I_{DD} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
3. Includes all peripherals that cannot have clocks gated in the Clock Control module.
4. Includes supply current from internal regulator and PLL0OSC (>20 MHz) or LPOSC0 (<=20 MHz).
5. Flash execution numbers use 2 wait states for 80 MHz and 0 wait states at 20 MHz or less.
6. RAM execution numbers use 0 wait states for all frequencies.
7. IDAC output current and IVC input current not included.
8. Bias current only. Does not include dynamic current from oscillator running at speed.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
External Oscillator (EXTOSC0)[8]	I_{EXTOSC}	FREQCN = 111	—	3.8	4.7	mA
		FREQCN = 110	—	840	950	µA
		FREQCN = 101	—	185	220	µA
		FREQCN = 100	—	65	80	µA
		FREQCN = 011	—	25	30	µA
		FREQCN = 010	—	10	15	µA
		FREQCN = 001	—	5	10	µA
		FREQCN = 000	—	3	8	µA
SARADC0, SARADC1	I_{SARADC}	Sampling at 1 Msps, highest power mode settings.	—	1.2	1.5	mA
		Sampling at 250 ksps, lowest power mode settings.	—	390	510	µA
Temperature Sensor	I_{TSENSE}		—	75	105	µA
Internal SAR Reference	I_{REFFS}	Normal Power Mode	—	680	750	µA
		Low Power Mode	—	160	190	µA
VREF0	I_{REFP}		—	75	100	µA
Comparator 0 (CMP0), Comparator 1 (CMP1)	I_{CMP}	CMPMD = 11	—	0.5	—	µA
		CMPMD = 10	—	3	—	µA
		CMPMD = 01	—	10	—	µA
		CMPMD = 00	—	25	—	µA
Capacitive Sensing (CAPSENSE0)	I_{CS}	Continuous Conversions	—	55	80	µA
IDAC0[7], IDAC1[7]	I_{IDAC}		—	75	90	µA
IVC0[7]	I_{IVC}	I_{IN} = 0	—	1.5	2.5	µA
Voltage Supply Monitor (VMON0)	I_{VMON}		—	15	25	µA

Notes:

1. Perhipheral currents drop to zero when peripheral clock and peripheral are disabled, unless otherwise noted.
2. Currents are additive. For example, where I_{DD} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
3. Includes all peripherals that cannot have clocks gated in the Clock Control module.
4. Includes supply current from internal regulator and PLL0OSC (>20 MHz) or LPOSC0 (<=20 MHz).
5. Flash execution numbers use 2 wait states for 80 MHz and 0 wait states at 20 MHz or less.
6. RAM execution numbers use 0 wait states for all frequencies.
7. IDAC output current and IVC input current not included.
8. Bias current only. Does not include dynamic current from oscillator running at speed.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Flash Current on VDD						
Write Operation	$I_{FLASH-W}$		—	—	8	mA
Erase Operation	$I_{FLASH-E}$		—	—	15	mA

Notes:
1. Perhipheral currents drop to zero when peripheral clock and peripheral are disabled, unless otherwise noted.
2. Currents are additive. For example, where I_{DD} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
3. Includes all peripherals that cannot have clocks gated in the Clock Control module.
4. Includes supply current from internal regulator and PLL0OSC (>20 MHz) or LPOSC0 (<=20 MHz).
5. Flash execution numbers use 2 wait states for 80 MHz and 0 wait states at 20 MHz or less.
6. RAM execution numbers use 0 wait states for all frequencies.
7. IDAC output current and IVC input current not included.
8. Bias current only. Does not include dynamic current from oscillator running at speed.

Table 3.3. Power Mode Wake Up Times

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 2 Wake Time	t_{PM2}		4	—	5	clocks
Power Mode 3 Fast Wake Time	t_{PM3FW}		—	425	—	µs
Power Mode 9 Wake Time	t_{PM9}		—	12	—	µs

Table 3.4. Reset and Supply Monitor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
V_{DD} High Supply Monitor Threshold (VDDHITHEN = 1)	V_{VDDMH}	Early Warning	2.10	2.20	2.30	V
		Reset	1.95	2.05	2.1	V
V_{DD} Low Supply Monitor Threshold (VDDHITHEN = 0)	V_{VDDML}	Early Warning	1.81	1.85	1.88	V
		Reset	1.70	1.74	1.77	V
V_{REGIN} Supply Monitor Threshold	V_{VREGM}	Early Warning	4.2	4.4	4.6	V
Power-On Reset (POR) Threshold	V_{POR}	Rising Voltage on V_{DD}	—	1.4	—	V
		Falling Voltage on V_{DD}	0.8	1	1.3	V
V_{DD} Ramp Time	t_{RMP}	Time to $V_{DD} \geq 1.8$ V	10	—	3000	µs
Reset Delay from POR	t_{POR}	Relative to $V_{DD} \geq V_{POR}$	3	—	100	ms
Reset Delay from non-POR source	t_{RST}	Time between release of reset source and code execution	—	10	—	µs
$\overline{\text{RESET}}$ Low Time to Generate Reset	t_{RSTL}		50	—	—	ns
Missing Clock Detector Response Time (final rising edge to reset)	t_{MCD}	$F_{AHB} > 1$ MHz	—	0.4	1	ms
Missing Clock Detector Trigger Frequency	F_{MCD}		—	7.5	13	kHz
V_{DD} Supply Monitor Turn-On Time	t_{MON}		—	2	—	µs

Table 3.5. On-Chip Regulators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
3.3 V Regulator Characteristics (VREG0, Supplied from VREGIN Pin)						
Output Voltage (at VDD pin)	V_{DDOUT}	$4 \le V_{REGIN} \le 5.5$ BGDIS = 0, SUSEN = 0	3.15	3.3	3.4	V
		$4 \le V_{REGIN} \le 5.5$ BGDIS = 0, SUSEN = 1	3.15	3.3	3.4	V
		$4 \le V_{REGIN} \le 5.5$ BGDIS = 1, SUSEN = X I_{DDOUT} = 500 µA	2.3	2.8	3.6	V
		$4 \le V_{REGIN} \le 5.5$ BGDIS = 1, SUSEN = X I_{DDOUT} = 5 mA	2.1	2.65	3.3	V
Output Current (at VDD pin)*	I_{DDOUT}	$4 \le V_{REGIN} \le 5.5$ BGDIS = 0, SUSEN = X	—	—	150	mA
		$4 \le V_{REGIN} \le 5.5$ BGDIS = 1, SUSEN = X	—	—	5	mA
Output Load Regulation	V_{DDLR}	BGDIS = 0	—	0.1	1	mV/mA
Output Capacitance	C_{VDD}		1	—	10	µF

***Note:** Total current VREG0 is capable of providing. Any current consumed by the SiM3C1xx reduces the current available to external devices powered from VDD.

Table 3.6. External Regulator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input Voltage Range (at VREGIN)	V_{REGIN}		3.0	—	3.6	V
Output Voltage (at EXREGOUT)	$V_{EXREGOUT}$	Programmable in 100 mV steps	1.8	—	3.6	V
NPN Current Drive	I_{NPN}	400 mV Dropout	12	—	—	mA
PNP Current Drive	I_{PNP}	$V_{EXREGBD} > V_{REGIN}$- 1.5 V	–6	—	—	mA
EXREGBD Voltage (PNP Mode)	$V_{EXREGBD}$	V_{REGIN} >= 3.5 V	V_{REGIN} – 2.0	—	—	V
		V_{REGIN} < 3.5 V	1.5	—	—	V
Standalone Mode Output Current	$I_{EXTREGBD}$	400 mV Dropout	—	—	11.5	mA
External Capacitance with External BJT	C_{BJT}		4.7	—	—	µF
Standalone Mode Load Regulation	$LR_{STAND-ALONE}$		—	1	—	mV/mA
Standalone Mode External Capacitance	$C_{STAND-ALONE}$		47	—	—	nF
Current Limit Range	I_{LIMIT}	1 Ω Sense Resistor	10	—	720	mA
Current Limit Accuracy			—	—	10	%
Foldback Limit Accuracy			—	—	20	%
Current Sense Resistor	R_{SENSE}		—	—	1	Ω
Internal Pull-Down	R_{PD}		—	5	—	kΩ
Internal Pull-Up	R_{PU}		—	10	—	kΩ
Current Sensor						
Sensing Pin Voltage	$V_{EXTREGSP}$ $V_{EXTREGSN}$	Measured at EXTREGSP or EXTREGSN pin	2.2	—	V_{REGIN}	V
Differential Sensing Voltage	V_{DIFF}	($V_{EXTREGSP}$ – $V_{EXTREGSN}$)	10	—	1600	mV
Current at EXTREGSN Pin	$I_{EXTREGSN}$		—	8	—	µA
Current at EXTREGSP Pin	$I_{EXTREGSP}$		—	V_{DIFF} x 200 + 12	—	µA

Table 3.7. Flash Memory

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Write Time[1]	t_{WRITE}	One 16-bit Half Word	20	21	22	µs
Erase Time[1]	t_{ERASE}	One Page	20	21	22	ms
	t_{ERALL}	Full Device	20	21	22	ms
V_{DD} Voltage During Programming	V_{PROG}		1.8	—	3.6	V
Endurance (Write/Erase Cycles)	N_{WE}		20k	100k	—	Cycles
Retention[2]	t_{RET}	T_A = 25 °C, 1k Cycles	10	100	—	Years

Notes:
1. Does not include sequencing time before and after the write/erase operation, which may take up to 35 µs. During a sequential write operation, this extra time is only taken prior to the first write and after the last write.
2. Additional Data Retention Information is published in the Quarterly Quality and Reliability Report.

Table 3.8. Internal Oscillators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Phase-Locked Loop (PLL0OSC)						
Calibrated Output Frequency*	$f_{PLL0OSC}$	Full Temperature and Supply Range	77	79	80	MHz
Power Supply Sensitivity*	$PSS_{PLL0OSC}$	T_A = 25 °C, Fout = 79 MHz	—	430	—	ppm/V
Temperature Sensitivity*	$TS_{PLL0OSC}$	V_{DD} = 3.3 V, Fout = 79 MHz	—	95	—	ppm/°C
Adjustable Output Frequency Range	$f_{PLL0OSC}$		23	—	80	MHz
Lock Time	$t_{PLL0LOCK}$	f_{REF} = 20 MHz, $f_{PLL0OSC}$ = 80 MHz, M=24, N=99, LOCKTH = 0	—	1.7	—	µs
		f_{REF} = 32 kHz, $f_{PLL0OSC}$ = 80 MHz, M=0, N=2440, LOCKTH = 0	—	91	—	µs

***Note:** PLL0OSC in free-running oscillator mode.

Table 3.8. Internal Oscillators (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Low Power Oscillator (LPOSC0)						
Oscillator Frequency	f_{LPOSC}	Full Temperature and Supply Range	19	20	21	MHz
		T_A = 25 °C, V_{DD} = 3.3 V	19.5	20	20.5	MHz
Divided Oscillator Frequency	f_{LPOSCD}	Full Temperature and Supply Range	2.375	2.5	2.625	MHz
Power Supply Sensitivity	PSS_{LPOSC}	T_A = 25 °C	—	0.5	—	%/V
Temperature Sensitivity	TS_{LPOSC}	V_{DD} = 3.3 V	—	55	—	ppm/°C
Low Frequency Oscillator (LFOSC0)						
Oscillator Frequency	f_{LFOSC}	Full Temperature and Supply Range	13.4	16.4	19.7	kHz
		T_A = 25 °C, V_{DD} = 3.3 V	15.8	16.4	17.3	kHz
Power Supply Sensitivity	PSS_{LFOSC}	T_A = 25 °C	—	2.4	—	%/V
Temperature Sensitivity	TS_{LFOSC}	V_{DD} = 3.3 V	—	0.2	—	%/°C
RTC0 Oscillator (RTC0OSC)						
Missing Clock Detector Trigger Frequency	f_{RTCMCD}		—	8	15	kHz
RTC Robust Duty Cycle Range	DC_{RTC}		25	—	55	%
***Note:** PLL0OSC in free-running oscillator mode.						

Table 3.9. External Oscillator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
External Input CMOS Clock Frequency*	f_{CMOS}		0	—	50	MHz
External Input CMOS Clock High Time	t_{CMOSH}		9	—	—	ns
External Input CMOS Clock Low Time	t_{CMOSL}		9	—	—	ns
External Crystal Clock Frequency	f_{XTAL}		0.01	—	30	MHz
***Note:** Minimum of 10 kHz during debug operations.						

Table 3.10. SAR ADC

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Resolution	N_{bits}	12 Bit Mode		12		Bits
		10 Bit Mode		10		Bits
Supply Voltage Requirements (VDD)	V_{ADC}	High Speed Mode	2.2	—	3.6	V
		Low Power Mode	1.8	—	3.6	V
Throughput Rate (High Speed Mode)	f_S	12 Bit Mode	—	—	250	ksps
		10 Bit Mode	—	—	1	Msps
Throughput Rate (Low Power Mode)	f_S	12 Bit Mode	—	—	62.5	ksps
		10 Bit Mode	—	—	250	ksps
Tracking Time	t_{TRK}	High Speed Mode	230	—	—	ns
		Low Power Mode	450	—	—	ns
SAR Clock Frequency	f_{SAR}	High Speed Mode	—	—	16.24	MHz
		Low Power Mode	—	—	4	MHz
Conversion Time	t_{CNV}	10-Bit Conversion, SAR Clock = 16 MHz, APB Clock = 40 MHz		762.5		ns
Sample/Hold Capacitor	C_{SAR}	Gain = 1	—	5	—	pF
		Gain = 0.5	—	2.5	—	pF
Input Pin Capacitance	C_{IN}	High Quality Inputs	—	18	—	pF
		Normal Inputs	—	20	—	pF
Input Mux Impedance	R_{MUX}	High Quality Inputs	—	300	—	Ω
		Normal Inputs	—	550	—	Ω
Voltage Reference Range	V_{REF}		1	—	V_{DD}	V
Input Voltage Range[1]	V_{IN}	Gain = 1	0	—	V_{REF}	V
		Gain = 0.5	0	—	$2xV_{REF}$	V
Power Supply Rejection Ratio	$PSRR_{ADC}$		—	70	—	dB
DC Performance						
Integral Nonlinearity	INL	12 Bit Mode[2]	—	±1	±1.9	LSB
		10 Bit Mode	—	±0.2	±0.5	LSB

Notes:
1. Absolute input pin voltage is limited by the lower of the supply at VDD and VIO.
2. INL and DNL specifications for 12-bit mode do not include the first or last four ADC codes.
3. The maximum code in 12-bit mode is 0xFFFC. The Slope Error is referenced from the maximum code.

Table 3.10. SAR ADC (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Differential Nonlinearity (Guaranteed Monotonic)	DNL	12 Bit Mode[2]	–1	±0.7	1.8	LSB
		10 Bit Mode	—	±0.2	±0.5	LSB
Offset Error (using VREFGND)	E_{OFF}	12 Bit Mode, VREF =2.4 V	–2	0	2	LSB
		10 Bit Mode, VREF =2.4 V	–1	0	1	LSB
Offset Temperatue Coefficient	TC_{OFF}		—	0.004	—	LSB/°C
Slope Error[3]	E_M	12 Bit Mode	–0.07	–0.02	0.02	%
Dynamic Performance with 10 kHz Sine Wave Input 1 dB below full scale, Max throughput						
Signal-to-Noise	SNR	12 Bit Mode	62	66	—	dB
		10 Bit Mode	58	60	—	dB
Signal-to-Noise Plus Distortion	SNDR	12 Bit Mode	62	66	—	dB
		10 Bit Mode	58	60	—	dB
Total Harmonic Distortion (Up to 5th Harmonic)	THD	12 Bit Mode	—	78	—	dB
		10 Bit Mode	—	77	—	dB
Spurious-Free Dynamic Range	SFDR	12 Bit Mode	—	–79	—	dB
		10 Bit Mode	—	–74	—	dB

Notes:
1. Absolute input pin voltage is limited by the lower of the supply at VDD and VIO.
2. INL and DNL specifications for 12-bit mode do not include the first or last four ADC codes.
3. The maximum code in 12-bit mode is 0xFFFC. The Slope Error is referenced from the maximum code.

Table 3.11. IDAC

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Performance						
Resolution	N_{bits}			10		Bits
Integral Nonlinearity	INL		—	±0.5	±2	LSB
Differential Nonlinearity (Guaranteed Monotonic)	DNL		—	±0.5	±1	LSB
Output Compliance Range	V_{OCR}		—	—	V_{DD} – 1.0	V
Full Scale Output Current	I_{OUT}	2 mA Range	2.0	2.046	2.10	mA
		1 mA Range	0.99	1.023	1.05	mA
		0.5 mA Range	493	511.5	525	µA
Offset Error	E_{OFF}		—	250	—	nA
Full Scale Error Tempco	TC_{FS}	2 mA Range	—	100	—	ppm/°C
VDD Power Supply Rejection Ratio		2 mA Range	—	-220	—	ppm/V
Test Load Impedance (to V_{SS})	R_{TEST}		—	1	—	kΩ
Dynamic Performance						
Output Settling Time to 1/2 LSB		min output to max output	—	1.2	—	µs
Startup Time			—	3	—	µs

Table 3.12. Capacitive Sense

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Single Conversion Time (Default Configuration)	t_{single}	12-bit Mode	—	25	—	µs
		13-bit Mode	—	27	—	µs
		14-bit Mode	—	29	—	µs
		16-bit Mode	—	33	—	µs
Maximum External Capacitive Load	C_L	Highest Gain Setting (default)	—	45	—	pF
		Lowest Gain Setting	—	500	—	pF
Maximum External Series Impedance	C_L	Highest Gain Setting (default)	—	50	—	kΩ

Table 3.13. Current-to-Voltage Converter (IVC)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Supply Voltage (VDD)	V_{DDIVC}		2.2	—	3.6	V
Input Pin Voltage	V_{IN}		2.2	—	VDD	V
Minimum Input Current (source)	I_{IN}		100	—	—	µA
Integral Nonlinearity	INL_{IVC}		–0.6	—	0.6	%
Full Scale Output	V_{IVCOUT}		—	1.65	—	V
Slope	M_{IVC}	Input Range 1 mA (INxRANGE = 101)	1.55	1.65	1.75	V/mA
		Input Range 2 mA (INxRANGE = 100)	795	830	860	mV/mA
		Input Range 3 mA (INxRANGE = 011)	525	550	570	mV/mA
		Input Range 4 mA (INxRANGE = 010)	390	415	430	mV/mA
		Input Range 5 mA (INxRANGE = 001)	315	330	340	mV/mA
		Input Range 6 mA (INxRANGE = 000)	260	275	285	mV/mA
Settling Time to 0.1%	V_{IVCOUT}		—	—	500	ns

Table 3.14. Voltage Reference Electrical Characteristics

V_{DD} = 1.8 to 3.6 V, –40 to +85 °C unless otherwise specified.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Internal Fast Settling Reference						
Output Voltage	V_{REFFS}	–40 to +85 °C, V_{DD} = 1.8–3.6 V	1.62	1.65	1.68	V
Temperature Coefficient	TC_{REFFS}		—	50	—	ppm/°C
Turn-on Time	t_{REFFS}		—	—	1.5	µs
Power Supply Rejection	$PSRR_{REFFS}$		—	400	—	ppm/V
On-Chip Precision Reference (VREF0)						
Valid Supply Range	V_{DD}	VREF2X = 0	1.8	—	3.6	V
		VREF2X = 1	2.7	—	3.6	V
Output Voltage	V_{REFP}	25 °C ambient, VREF2X = 0	1.195	1.2	1.205	V
		25 °C ambient, VREF2X = 1	2.39	2.4	2.41	V
Short-Circuit Current	I_{SC}		—	—	10	mA
Temperature Coefficient	TC_{VREFP}		—	25	—	ppm/°C
Load Regulation	LR_{VREFP}	Load = 0 to 200 µA to VREFGND	—	4.5	—	ppm/µA
Load Capacitor	C_{VREFP}	Load = 0 to 200 µA to VREFGND	0.1	—	—	µF
Turn-on Time	$t_{VREFPON}$	4.7 µF tantalum, 0.1 µF ceramic bypass	—	3.8	—	ms
		0.1 µF ceramic bypass	—	200	—	µs
Power Supply Rejection	$PSRR_{VREFP}$	VREF2X = 0	—	320	—	ppm/V
		VREF2X = 1	—	560	—	ppm/V
External Reference						
Input Current	I_{EXTREF}	Sample Rate = 250 ksps; VREF = 3.0 V	—	5.25	—	µA

Table 3.15. Temperature Sensor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Offset	V_{OFF}	T_A = 0 °C	—	760	—	mV
Offset Error*	E_{OFF}	T_A = 0 °C	—	±14	—	mV
Slope	M		—	2.8	—	mV/°C
Slope Error*	E_M		—	±120	—	µV/°C
Linearity			—	1	—	°C
Turn-on Time			—	1.8	—	µs
***Note:** Represents one standard deviation from the mean.						

Table 3.16. Comparator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Response Time, CMPMD = 00 (Highest Speed)	t_{RESP0}	+100 mV Differential	—	100	—	ns
		–100 mV Differential	—	150	—	ns
Response Time, CMPMD = 11 (Lowest Power)	t_{RESP3}	+100 mV Differential	—	1.4	—	µs
		–100 mV Differential	—	3.5	—	µs
Positive Hysteresis Mode 0 (CPMD = 00)	HYS_{CP+}	CMPHYP = 00	—	0.4	—	mV
		CMPHYP = 01	—	8	—	mV
		CMPHYP = 10	—	16	—	mV
		CMPHYP = 11	—	33	—	mV
Negative Hysteresis Mode 0 (CPMD = 00)	HYS_{CP-}	CMPHYN = 00	—	0.4	—	mV
		CMPHYN = 01	—	–8	—	mV
		CMPHYN = 10	—	–16	—	mV
		CMPHYN = 11	—	–33	—	mV
Positive Hysteresis Mode 1 (CPMD = 01)	HYS_{CP+}	CMPHYP = 00	—	0.5	—	mV
		CMPHYP = 01	—	6	—	mV
		CMPHYP = 10	—	12	—	mV
		CMPHYP = 11	—	24	—	mV
Negative Hysteresis Mode 1 (CPMD = 01)	HYS_{CP-}	CMPHYN = 00	—	0.5	—	mV
		CMPHYN = 01	—	–6.0	—	mV
		CMPHYN = 10	—	–12	—	mV
		CMPHYN = 11	—	–24	—	mV
Positive Hysteresis Mode 2 (CPMD = 10)	HYS_{CP+}	CMPHYP = 00	—	0.6	—	mV
		CMPHYP = 01	—	4.5	—	mV
		CMPHYP = 10	—	9.5	—	mV
		CMPHYP = 11	—	19	—	mV
Negative Hysteresis Mode 2 (CPMD = 10)	HYS_{CP-}	CMPHYN = 00	—	0.6	—	mV
		CMPHYN = 01	—	–4.5	—	mV
		CMPHYN = 10	—	–9.5	—	mV
		CMPHYN = 11	—	–19	—	mV

Table 3.16. Comparator (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Positive Hysteresis Mode 3 (CPMD = 11)	HYS_{CP+}	CMPHYP = 00	—	1.4	—	mV
		CMPHYP = 01	—	4	—	mV
		CMPHYP = 10	—	8	—	mV
		CMPHYP = 11	—	16	—	mV
Negative Hysteresis Mode 3 (CPMD = 11)	HYS_{CP-}	CMPHYN = 00	—	1.4	—	mV
		CMPHYN = 01	—	–4	—	mV
		CMPHYN = 10	—	–8	—	mV
		CMPHYN = 11	—	–16	—	mV
Input Range (CP+ or CP–)	V_{IN}		–0.25	—	V_{DD}+0.25	V
Input Pin Capacitance	C_{CP}	PB2 Pins	—	7.5	—	pF
		PB3 Pins	—	10.5	—	pF
Common-Mode Rejection Ratio	$CMRR_{CP}$		—	75	—	dB
Power Supply Rejection Ratio	$PSRR_{CP}$		—	72	—	dB
Input Offset Voltage	V_{OFF}		–10	0	10	mV
Input Offset Tempco	TC_{OFF}		—	3.5	—	µV/°C
Reference DAC Resolution	N_{Bits}			6		bits

Table 3.17. Port I/O

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Standard I/O (PB0, PB1, and PB2), 5 V Tolerant I/O (PB3), and $\overline{\text{RESET}}$						
Output High Voltage*	V_{OH}	Low Drive, I_{OH} = –2 mA	V_{IO} – 0.7	—	—	V
		High Drive, I_{OH} = –5 mA	V_{IO} – 0.7	—	—	V
Output Low Voltage*	V_{OL}	Low Drive, I_{OL} = 3 mA	—	—	0.6	V
		High Drive, I_{OL} = 12.5 mA	—	—	0.6	V
Input High Voltage	V_{IH}	1.8 ≤ V_{IO} ≤ 2.0	0.7 x V_{IO}	—	—	V
		2.0 ≤ V_{IO} ≤ 3.6	V_{IO} – 0.6	—	—	V
Input Low Voltage	V_{IL}		—	—	0.6	V
Pin Capacitance	C_{IO}	PB0, PB1 and PB2 Pins	—	4	—	pF
		PB3 Pins	—	7	—	pF
Weak Pull-Up Current (Input Voltage = 0 V)	I_{PU}	V_{IO} = 1.8	–6	–3.5	–2	µA
		V_{IO} = 3.6	–30	–20	–10	µA
Input Leakage (Pullups off or Analog)	I_{LK}	0 ≤ V_{IN} ≤ V_{IO}	–1	—	1	µA
Input Leakage Current of Port Bank 3 I/O, V_{IN} above V_{IO}	I_L	V_{IO} < V_{IN} < V_{IO}+2.0 V (pins without EXREG functions)	0	5	150	µA
		V_{IO} < V_{IN} < V_{REGIN} (pins with EXREG functions)	0	5	150	µA
High Drive I/O (PB4)						
Output High Voltage	V_{OH}	Standard Mode, Low Drive, I_{OH} = –3 mA	V_{IOHD} – 0.7	—	—	V
		Standard Mode, High Drive, I_{OH} = –10 mA	V_{IOHD} – 0.7	—	—	V
Output Low Voltage	V_{OL}	Standard Mode, Low Drive, I_{OH} = 3 mA	—	—	0.6	V
		Standard Mode, High Drive, I_{OH} = 12.5 mA	—	—	0.6	V
Output Rise Time	t_R	Slew Rate Mode 0, V_{IOHD} = 5 V	—	50	—	ns
		Slew Rate Mode 1, V_{IOHD} = 5 V	—	300	—	ns
		Slew Rate Mode 2, V_{IOHD} = 5 V	—	1	—	µs
		Slew Rate Mode 3, V_{IOHD} = 5 V	—	3	—	µs

***Note:** $\overline{\text{RESET}}$ does not drive to logic high. Specifications for $\overline{\text{RESET}}$ V_{OL} adhere to the low drive setting.